

## CEER-S-188

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PHOTOVOLTAIC CELL TECHNOLOGIES

Je 7. PYTLINSKI

CENTER FOR ENERGY AND ENVIRONMENT RESEARCH

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Proceedings of the VITIth Inter-American Conference on Materials Technology, June 25-30, 1984,

San Juan, Puerto Rico.

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Fig. 2. Cross-Sectional view of typical pa

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One advantage of Si and GaAs

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Growth of Si) saves the cost

Solar cell technology

Polysilicon is used for the

cell surface passivation

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(as shown in Fig. 8)

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